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(57) **ABSTRACT**

Efficient cleaning is possible although the film qualities and thicknesses of a reaction tube and a gas supply nozzle are different. There is provided a method of manufacturing a semiconductor device. The method includes forming a film on a substrate, performing a first cleaning process to remove a first deposition substance attached to an inner wall of a gas introducing part, and performing a second cleaning process to remove a second deposition substance attached to an inside of a process chamber and having a chemical composition different from that of the first deposition substance. In the first cleaning process, cleaning conditions are set according to the accumulated supply time of a first source gas supplied to the inside of the process chamber through the gas introducing part, and in the second cleaning process, cleaning conditions are set according to the accumulated thickness of a film formed on the substrate.

5 Claims, 8 Drawing Sheets

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438/680, 694; 257/E21.002
See application file for complete search history.

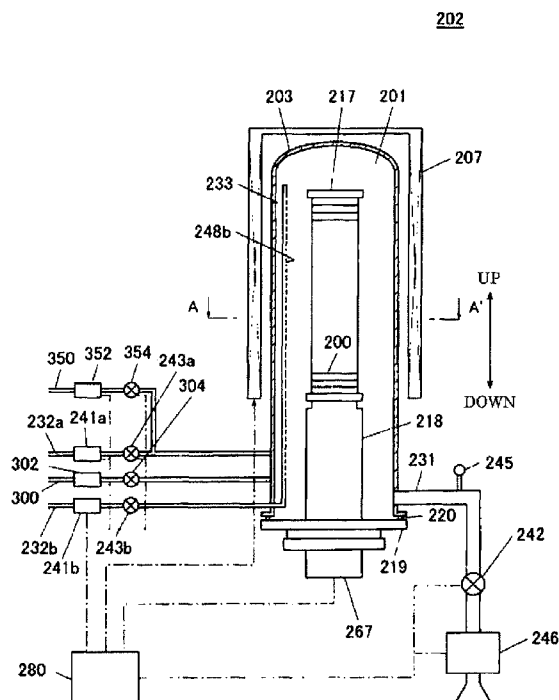


Fig. 1

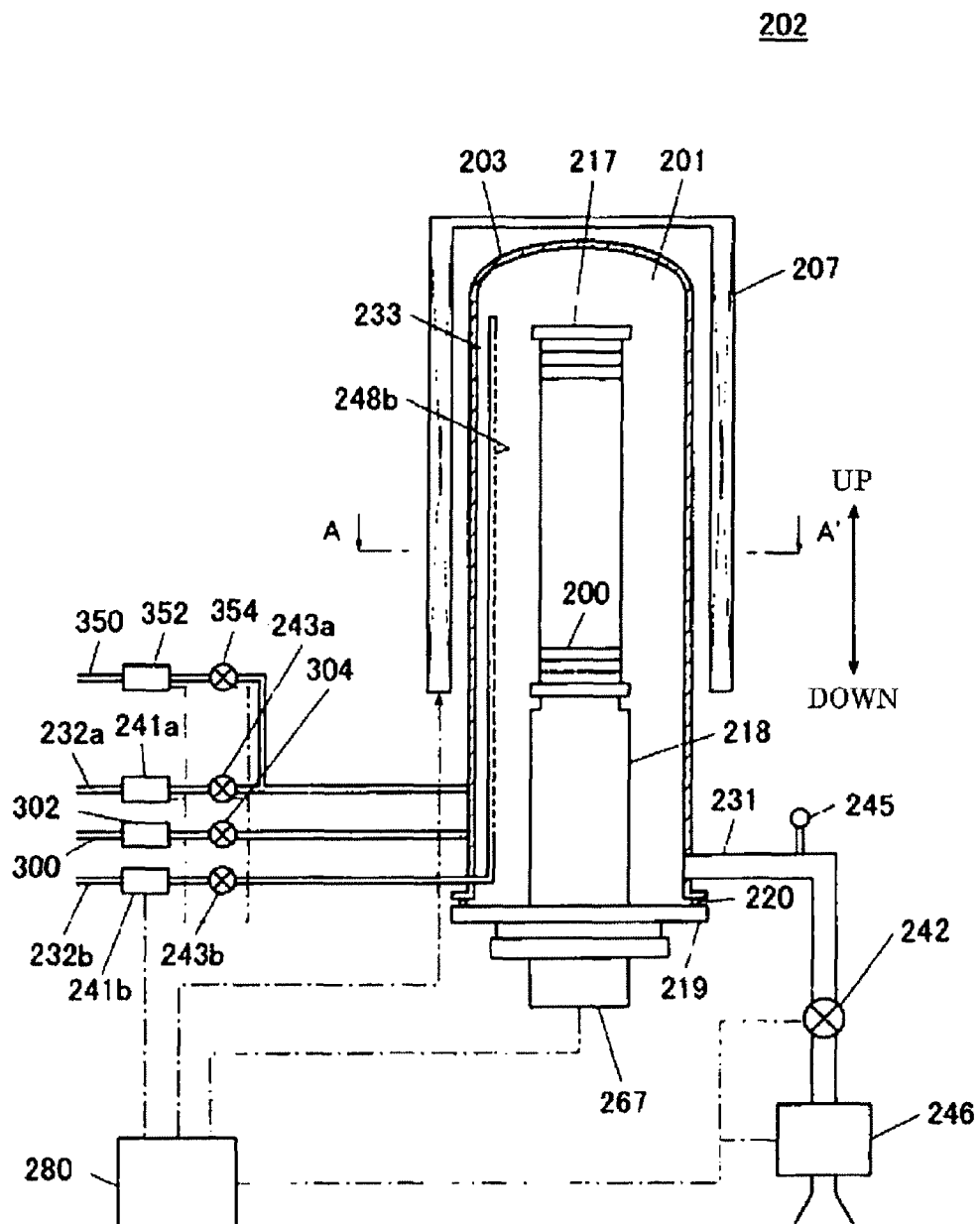


Fig. 2

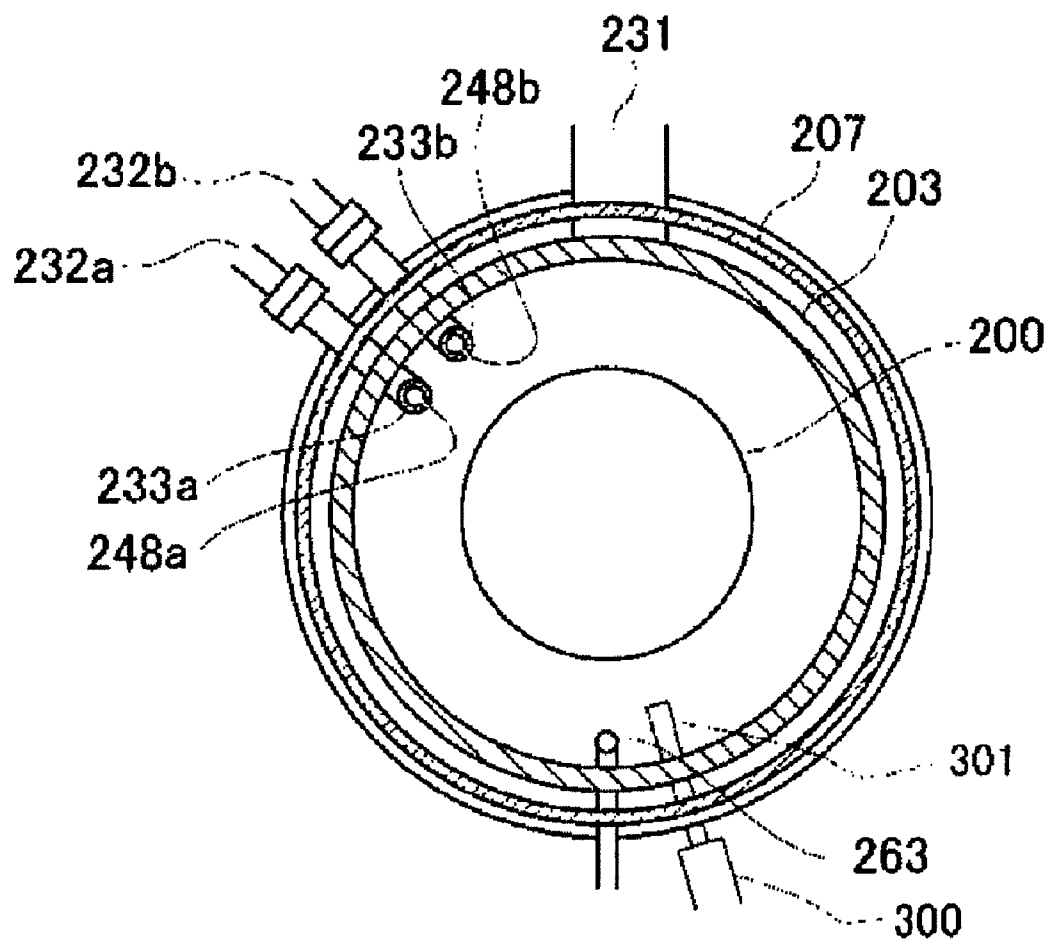


Fig. 3

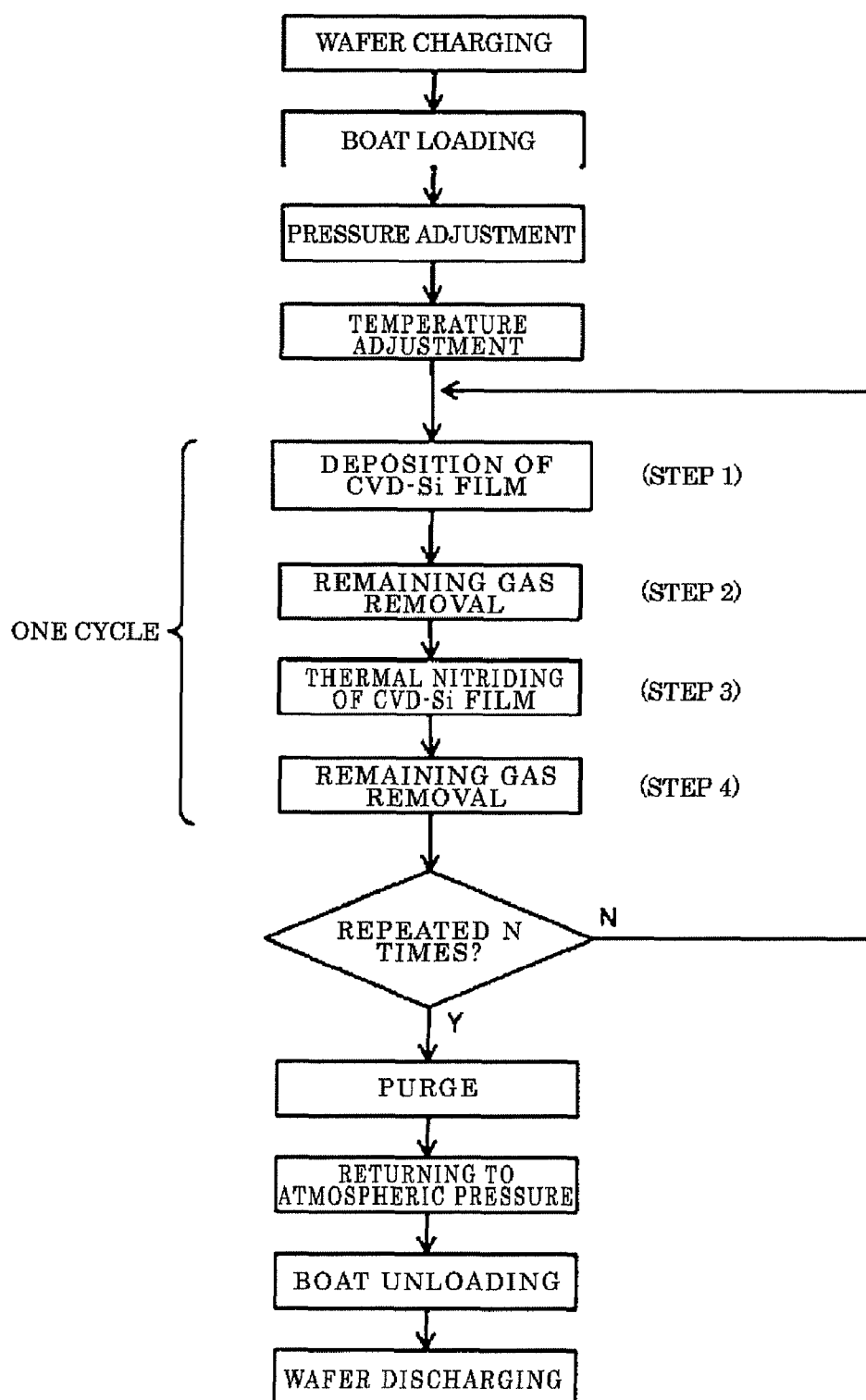


Fig. 4

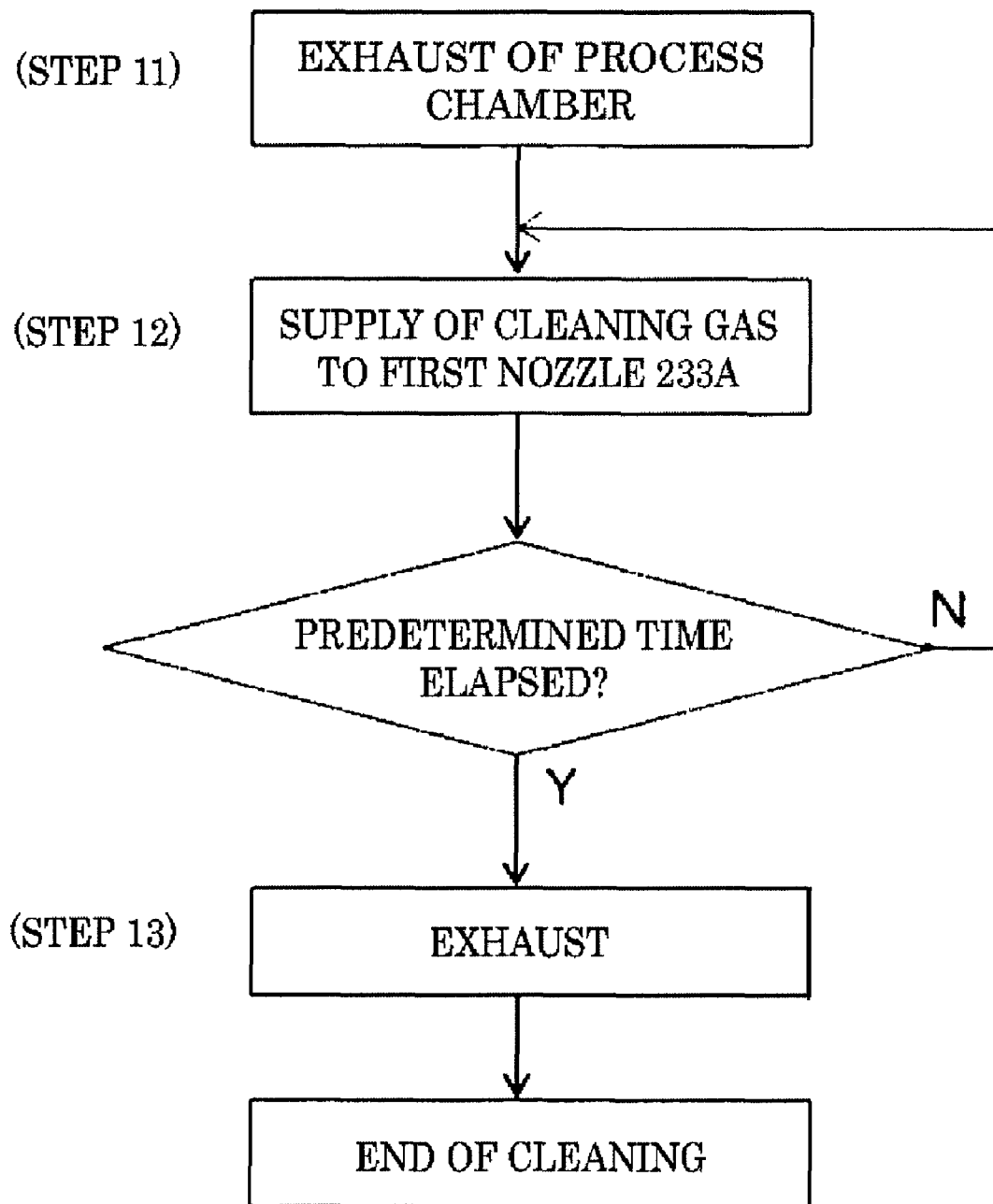


Fig. 5

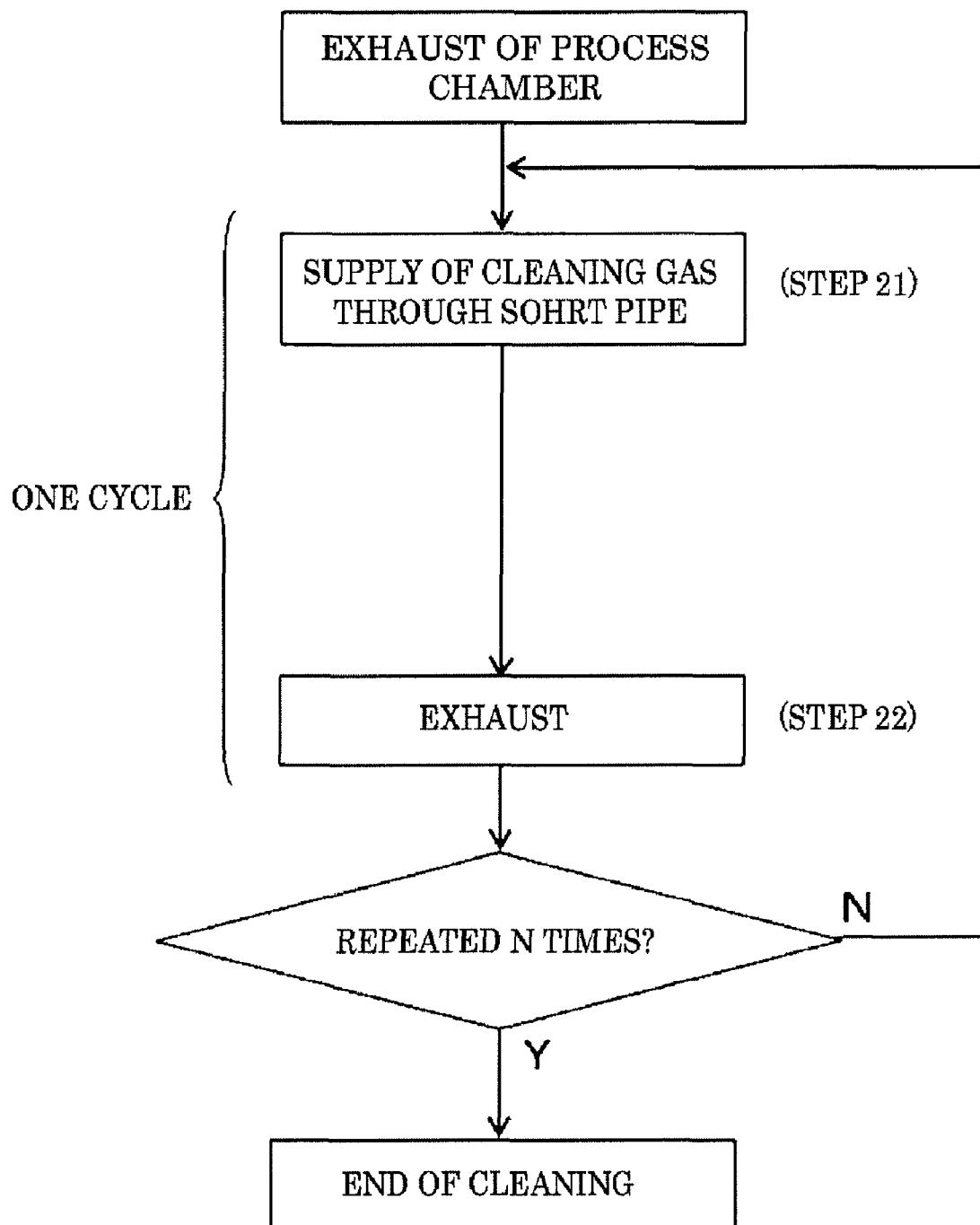


Fig. 6

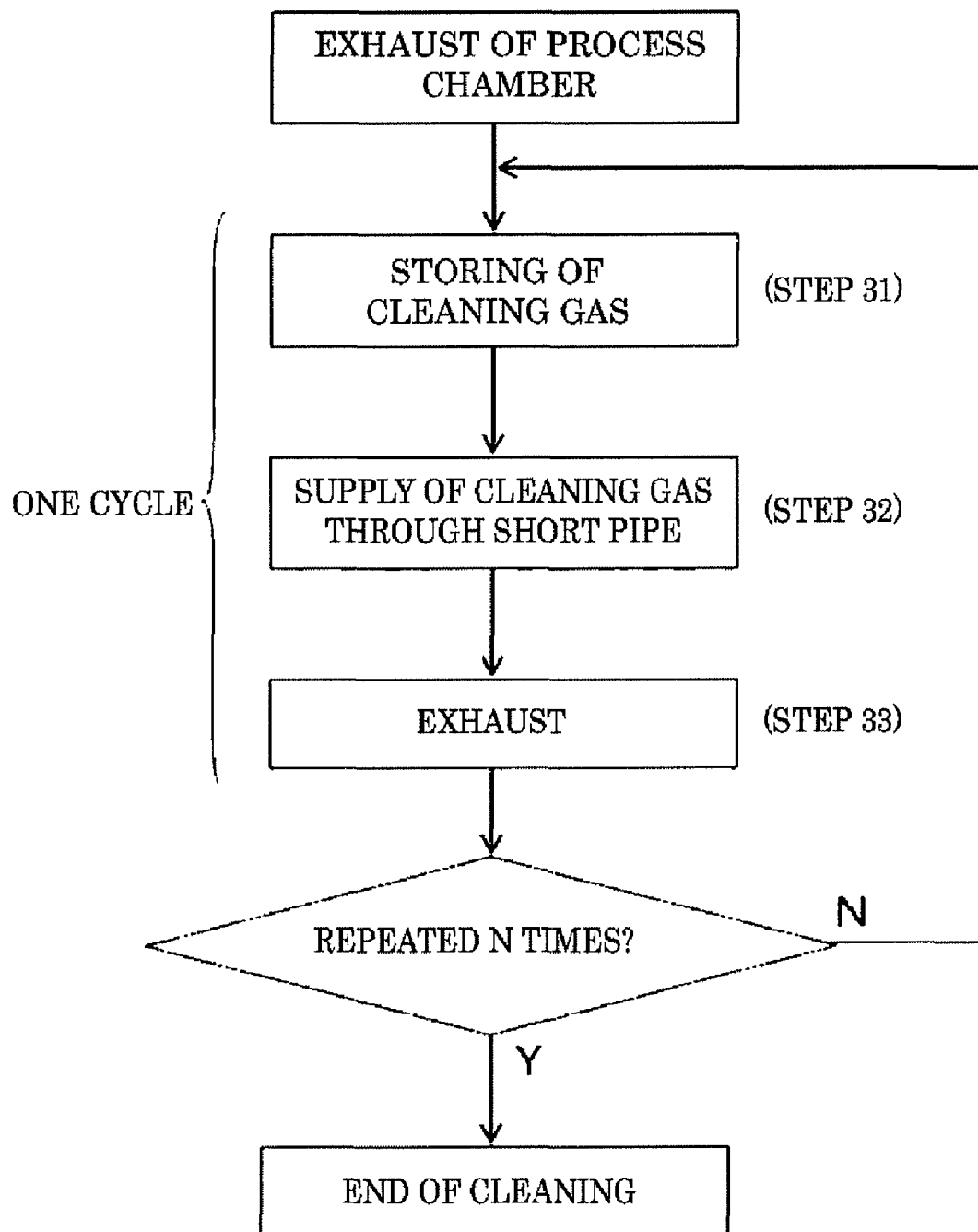


Fig. 7A

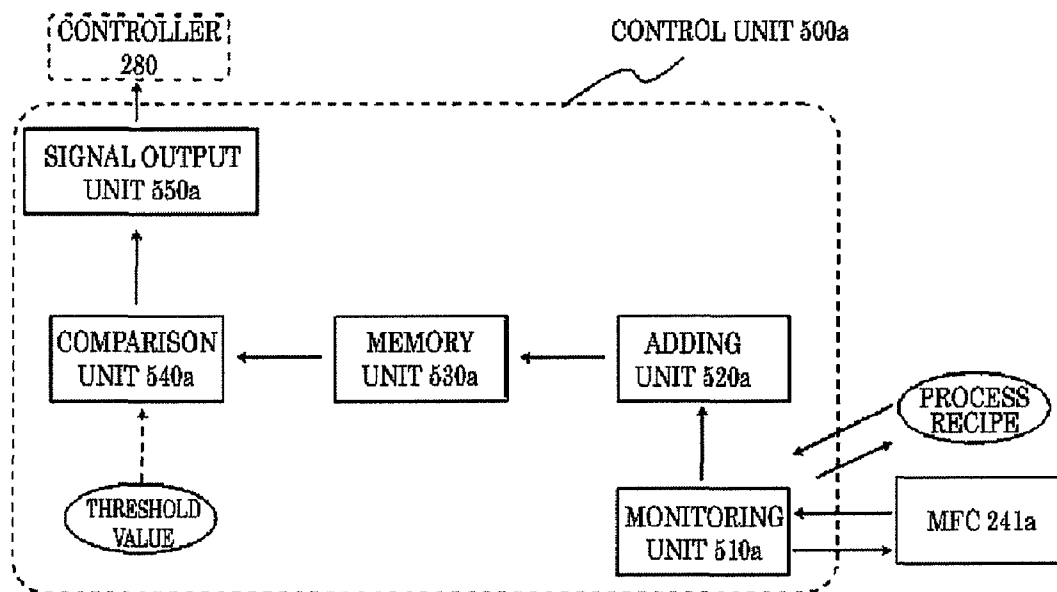


Fig. 7B

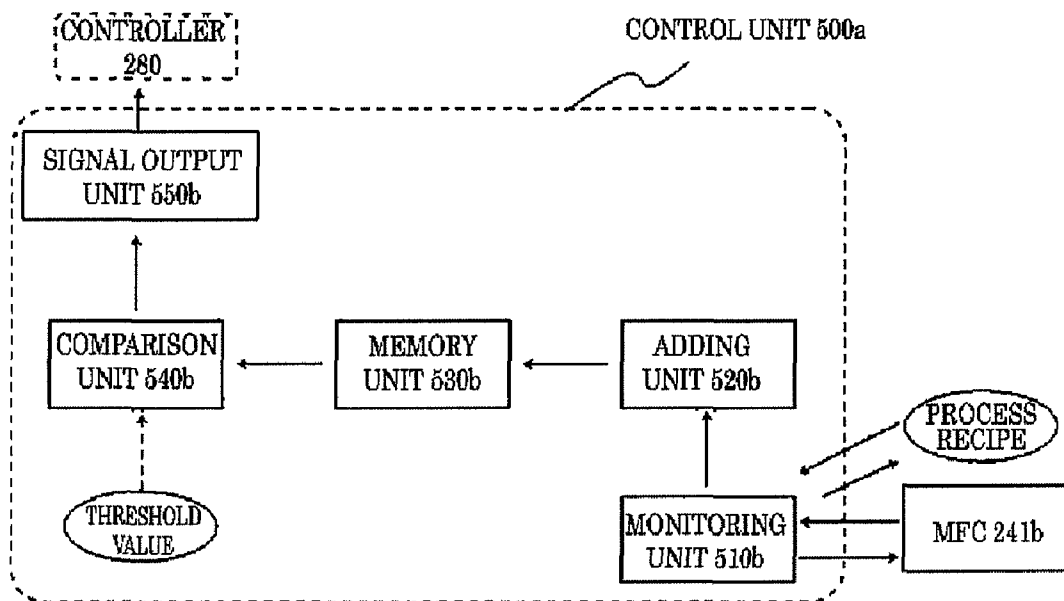
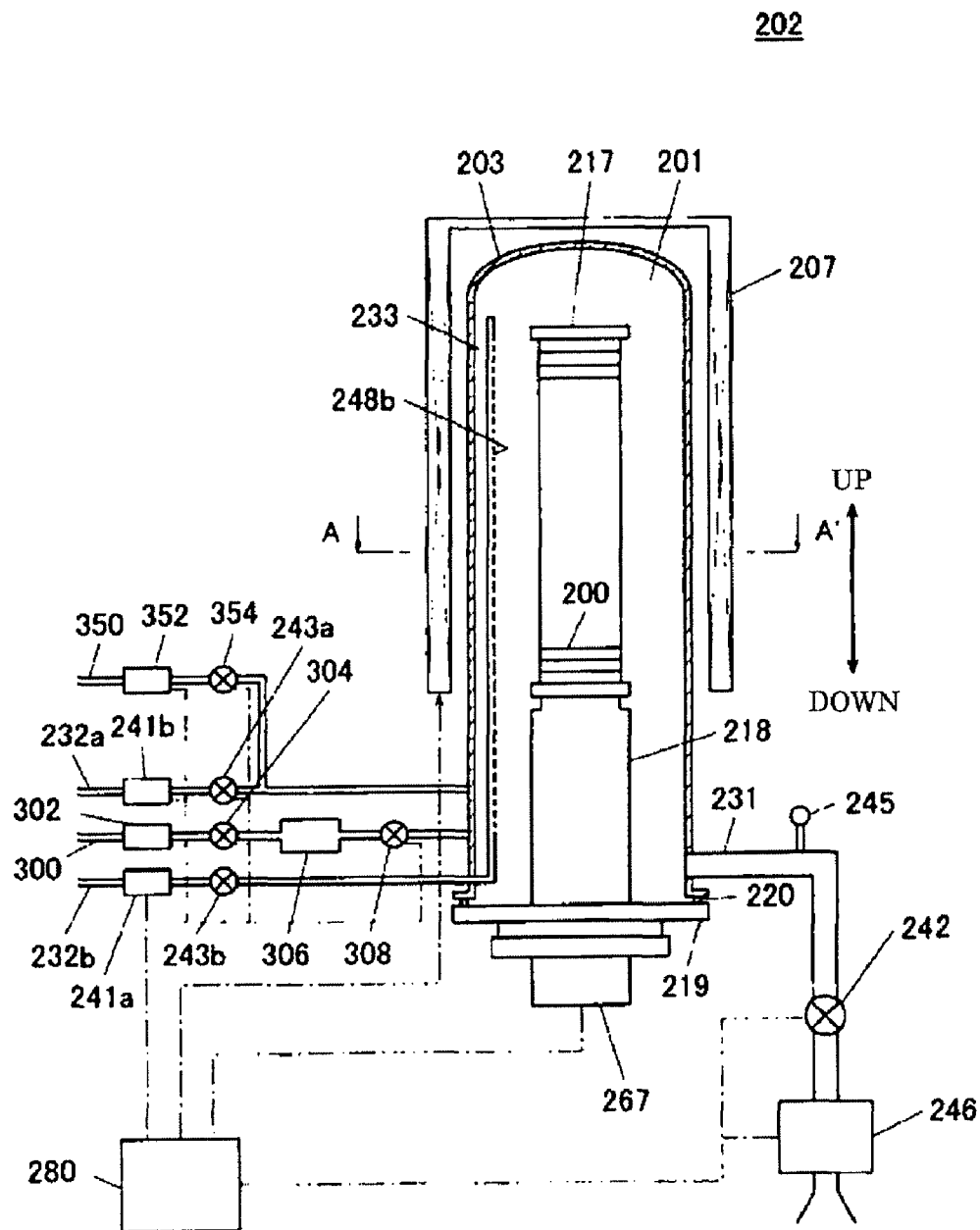


Fig. 8



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METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, CLEANING METHOD AND CLEANING CONTROL APPARATUS

CROSS-REFERENCE TO RELATED PATENT APPLICATION

This U.S. non-provisional patent application claims priority under 35 U.S.C. § 119 of Japanese Patent Application Nos. 2008-329416, filed on Dec. 25, 2008, and 2009-267530, filed on Nov. 25, 2009, in the Japanese Patent Office, the entire contents of which are hereby incorporated by reference.

BACKGROUND OF THE INVENTION

1. Field of the Invention

The present invention relates to a method of manufacturing a semiconductor device, a cleaning method, and a cleaning control apparatus. More particularly, the present invention relates to a method of manufacturing a semiconductor device by supplying a process (source) gas to the surface of a substrate to form a desired film on the substrate, and a cleaning method and a cleaning control apparatus.

2. Description of the Prior Art

In a conventional substrate processing apparatus, when a process gas is supplied, the process gas is distributed not only to the surface of a substrate but also to other parts (for example, the inside of a process chamber), and thus unnecessary films may be accumulated and deposited as attached substances. Such attached substances may include impurities harmful for a substrate processing process, and thus, substrates may be contaminated due to the attached substances.

Therefore, so as to prevent or suppress such a problem, in addition to the supply of a process gas to the process chamber, a cleaning gas is also supplied to the inside of the process chamber (particularly, parts where it is expected that substances are attached) so as to remove substances attached to the inside of the process chamber by converting the substances into harmless gas and then discharging the harmless gas. That is, self-cleaning is performed (for example, refer to Patent Document 1).

Patent Document 1

Japanese Patent No. 3985899

However, since at least a reaction tube configured to place a substrate therein and a process gas supply nozzle configured to supply a process gas to the reaction tube are disposed in the process chamber, different films may be deposited on the inside (inner wall or other parts) of the reaction tube and the inner wall of the process gas supply nozzle according to a method used to supply a process gas to the inside of the process chamber.

Exhaust resistance is caused according to the length of the gas supply nozzle or the shape of a gas supply hole, and if the exhaust resistance is high, the inside pressure of the gas supply nozzle becomes higher than the inside pressure of the reaction tube. In this case, generally, since the reaction rate of a process gas increases as pressure increases, the thickness of a film deposited on the inner wall of the gas supply nozzle becomes greater than the thickness of a film deposited on the inside of the reaction tube. Moreover, according to the kind of chemical reaction, the properties of films such as a crystalline structure may be changed.

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By using a silicon source and a nitriding source as process gases, a silicon nitride film can be formed on the surface of a substrate.

In this case, to prevent generation of a reaction byproduct, the process gases are supplied to a process chamber via separate gas supply nozzles. At this time, a silicon film may be formed, due to decomposition of the silicon source, on the inner wall of a first nozzle through which the silicon source is supplied, although formation of a film caused by decomposition of the nitriding source is not observed at the inner wall of a second nozzle through which the nitriding source is supplied. In addition, a silicon nitride film is formed on the inside of a reaction tube as an attached substance. That is, different films may be formed on the inside of the reaction tube and the inner wall of the gas supply nozzle.

In the case where films having different qualities and thicknesses are formed on the inside of the reaction tube and the inner wall of the gas supply nozzle, if a cleaning process is performed under normal conditions, there may arise disadvantages such as an increase of cleaning time, generation of contaminants, and damages on the reaction tube and the gas supply nozzle. Moreover, if a cleaning process is performed under normal conditions, the inner wall of the gas supply nozzle may be etched more rapidly than the inside of the reaction tube.

SUMMARY OF THE INVENTION

An object of the present invention is to provide a method of manufacturing a semiconductor device, a cleaning method, and a cleaning control apparatus that are designed to perform a cleaning process efficiently on the inside of a process chamber while reducing generation of contaminants and damages on a reaction tube and a gas supply nozzle.

According to an aspect of the present invention, there is provided a method of manufacturing a semiconductor device, comprising: loading a substrate into a process chamber; forming a film comprising a plurality of elements on the substrate by supplying a first source gas and second source gas into the process chamber through a first gas introducing part and a second gas introducing part, respectively, the first source gas comprising at least one of the plurality of elements and the second source gas comprising at least one of the plurality of elements other than those of the first source gas; unloading the substrate from the process chamber after the film is formed on the substrate; performing a first cleaning process so as to remove a first deposition substance attached to an inner wall of the first gas introducing part by supplying a cleaning gas to the first gas introducing part, the first deposition substance comprising the at least one of the plurality of elements of the first source gas as a main component, wherein a cleaning condition is set according to an accumulated supply time of the first source gas supplied into the process chamber through the first gas introducing part; and performing a second cleaning process so as to remove a second deposition substance attached to an inside of the process chamber and having a different chemical composition from that of the first deposition substance by supplying the cleaning gas into the process chamber through a third gas introducing part connected to a lower side of the process chamber at a position where the substrate is not placed, the second deposition substance comprising the plurality of elements as main components, wherein the cleaning condition is set according to an accumulated thickness of the film formed on the substrate.

According to another aspect of the present invention, there is provided a cleaning method for removing a film attached to an inside of a process chamber of a substrate processing

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apparatus which is used to form a film on a substrate by supplying a process gas to the substrate, the cleaning method comprising: setting pressure of the inside of the process chamber to a first pressure and intermittently supplying a cleaning gas to the inside of the process chamber; and setting the pressure of the inside of the process chamber to a second pressure higher than the first pressure and continuously supplying the cleaning gas to the inside of the process chamber.

According to another aspect of the present invention, there is provided a cleaning control apparatus for a process chamber or a silicon-containing gas supply system of a silicon nitride film forming apparatus which is used to form a silicon nitride film having a predetermined silicon/nitrogen composition ratio on a substrate by alternately supplying a silicon-containing gas having a predetermined molecular weight and a nitriding source gas having a predetermined molecular weight, the cleaning control apparatus comprising: a cleaning request signal output unit comprising a memory unit configured to store an accumulated supply amount of silicon-containing gas molecules supplied to an inside of the process chamber through the silicon-containing gas supply system, the cleaning request signal output unit being configured to output a cleaning request signal so as to request cleaning of the silicon-containing gas supply system if the accumulated supply amount of the silicon-containing gas molecules stored in the memory unit becomes equal to or greater than a preset accumulated supply amount of silicon-containing gas molecules; and a cleaning request signal output unit comprising a memory unit configured to store an accumulated supply amount of nitriding source gas molecules supplied to the inside of the process chamber through a nitriding source gas supply system, the cleaning request signal output unit being configured to output a cleaning request signal so as to request cleaning of the nitriding source gas supply system if the accumulated supply amount of the nitriding source gas molecules stored in the memory unit becomes equal to or greater than a preset accumulated supply amount of nitriding source gas molecules.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a schematic view illustrating a vertical process furnace of a substrate processing apparatus suitable for an embodiment of the present invention.

FIG. 2 is a sectional view taken from line A-A' of FIG. 1.

FIG. 3 is a flowchart for explaining a film-forming method according to an embodiment of the present invention.

FIG. 4 is a flowchart for explaining a cleaning method according to an embodiment of the present invention.

FIG. 5 is a flowchart for explaining a cleaning method according to an embodiment of the present invention.

FIG. 6 is a flowchart for explaining a cleaning method according to another embodiment of the present invention.

FIG. 7A and FIG. 7B are views illustrating control units according to an embodiment of the present invention.

FIG. 8 is a schematic view illustrating a vertical process furnace of a substrate processing apparatus suitable for another embodiment of the present invention.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

Embodiments of the present invention will be described hereinafter with reference to the attached drawings.

(1) Structure of Substrate Processing Apparatus

FIG. 1 is a schematic vertical sectional view illustrating a vertical process furnace 202 of a substrate processing apparatus

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suitable for an embodiment of the present invention. FIG. 2 is a sectional view taken from line A-A' of FIG. 1.

As shown in FIG. 1, the process furnace 202 includes a heater 207 used as a heating unit (heating mechanism). The heater 207 has a cylindrical shape and is vertically installed in a state where the heater 207 is supported on a heater base (not shown) which is a holding plate.

Inside the heater 207, a process tube 203 is installed concentrically with the heater 207 as a reaction tube. The process tube 203 is made of a heat-resistant material such as a quartz (SiO_2) or silicon carbide (SiC) and has a cylindrical shape with a closed top side and an opened bottom side. The hollow part of the process tube 203 forms a process chamber 201 and is configured to accommodate substrates such as wafers 200 by using a substrate holder such as a boat 217 (described later) in a manner such that the wafers 200 are horizontally positioned and vertically arranged in multiple stages.

At the lower side of the process chamber 201, a first nozzle 233a and a second nozzle 233b are installed as a first gas introducing part and a second gas introducing part, and a first gas supply pipe 232a and a second gas supply pipe 232b are connected to the first nozzle 233a and the second nozzle 233b, respectively. In this way, as gas supply passages for supplying a plurality of kinds of gases (in the current embodiment, two kinds of gases) to the inside of the process chamber 201, two gas supply pipes are installed. In the structure, the lower side of the process chamber 201 is a region where no wafer 200 is placed, and the lower side of the process chamber 201 is not a heating region.

At the first gas supply pipe 232a, a flowrate controller (flowrate control unit) such as a first mass flow controller (MFC) 241a, and an on-off valve such as a first valve 243a are sequentially installed from the upstream side of the first gas supply pipe 232a. In addition, the first nozzle 233a is connected to the leading end of the first gas supply pipe 232a. In an arc-shaped space between the inner wall of the process tube 203 constituting the process chamber 201 and wafers 200, the first nozzle 233a is installed in a manner such that the first nozzle 233a extends from the lower side to the upper side along the inner wall of the process tube 203 in a direction in which the wafers 200 are stacked. First gas supply holes 248a are formed through the lateral surface of the first nozzle 233a. Along the lower side to the upper side, the first gas supply holes 248a are formed in a manner that the first gas supply holes 248a have the same size and are arranged at the same pitch. A first gas supply system is mainly constituted by the first gas supply pipe 232a, the first MFC 241a, the first valve 243a, and the first nozzle 233a.

At the second gas supply pipe 232b, a flowrate controller (flowrate control unit) such as a second MFC 241b, and an on-off valve such as a second valve 243b are sequentially installed from the upstream side of the second gas supply pipe 232b. In addition, the second nozzle 233b is connected to the leading end of the second gas supply pipe 232b. In an arc-shaped space between the inner wall of the process tube 203 constituting the process chamber 201 and the wafers 200, the second nozzle 233b is installed in a manner such that the second nozzle 233b extends from the lower side to the upper side along the inner wall of the process tube 203 in a direction in which the wafers 200 are stacked. Second gas supply holes 248b are formed through the lateral surface of the second nozzle 233b. Along the lower side to the upper side, the second gas supply holes 248b are formed in a manner that the second gas supply holes 248b have the same size and are arranged at the same pitch. A second gas supply system is

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mainly constituted by the second gas supply pipe **232b**, the second MFC **241b**, the second valve **243b**, and the second nozzle **233b**.

For example, dichlorosilane (SiH_2Cl_2 , abbreviation: DCS) gas may be supplied from the first gas supply pipe **232a** to the inside of the process chamber **201** through the first MFC **241a**, the first valve **243a**, and the first nozzle **233a**. At this time, inert gas may be simultaneously supplied to the inside of the first gas supply pipe **232a**. In addition, ammonia (NH_3) gas may be supplied from the second gas supply pipe **232b** to the inside of the process chamber **201** through the second MFC **241b**, the second valve **243b**, and the second nozzle **233b**. At this time, inert gas may be simultaneously supplied to the inside of the second nozzle **233b**.

In addition, at the lower side of the process chamber **201**, a short pipe **301** is installed as a third gas introducing part. A first cleaning gas supply pipe **300** which is a cleaning gas supply passage is connected to the short pipe **301**. Cleaning gas is used for removing substances attached to the inside of the process chamber **201**. At the first cleaning gas supply pipe **300**, a flowrate controller (flowrate control unit) such as a third MFC **302**, and an on-off valve such as a third valve **304** are installed. Cleaning gas is introduced into the first cleaning gas supply pipe **300** for supplying the cleaning gas to the process chamber **201**.

A second cleaning gas supply pipe **350**, which is a cleaning gas supply passage separate from the first cleaning gas supply pipe **300**, is connected to the first gas supply pipe **232a**. At the second cleaning gas supply pipe **350**, a flowrate controller (flowrate control unit) such as a fourth MFC **352**, and an on-off valve such as a fourth valve **354** are installed. Cleaning gas is introduced into the second cleaning gas supply pipe **350** for supplying the cleaning gas to the process chamber **201** through the first gas supply pipe **232a**.

In addition, a gas exhaust pipe **231** is installed to exhaust the inside atmosphere of the process chamber **201**. A vacuum exhaust device such as a vacuum pump **246** is connected to the downstream side of the gas exhaust pipe **231** opposite to the process tube **203** through a pressure detector such as a pressure sensor **245** and a pressure regulator such as an auto pressure controller (APC) valve **242**. The APC valve **242** is an on-off valve, which can be opened and closed to start and stop vacuum evacuation of the inside of the process chamber **201** and can be adjusted in opened degree for pressure adjustment. While operating the pressure sensor **245**, by controlling the opened degree of the APC valve **242** based on pressure information detected by the pressure sensor **245**, the inside of the process chamber **201** can be vacuum-evacuated to a desired pressure (vacuum degree).

A seal cap **219** is installed as a furnace port cover capable of hermetically closing the opened bottom side of the process tube **203**. For example, the seal cap **219** is made of a metal such as stainless steel and has a disk shape. On the top surface of the seal cap **219**, an O-ring **220** is installed as a seal member. At a side of the seal cap **219** opposite to the process chamber **201**, a rotary mechanism **267** is installed to rotate a boat **217** (described later) which is a substrate holder. A rotation shaft (not shown) of the rotary mechanism **267** is connected to the boat **217** through the seal cap **219**. The rotary mechanism **267** is configured to rotate wafers **200** by rotating the boat **217**. The seal cap **219** is configured to be vertically moved by an elevating mechanism such as a boat elevator (not shown) which is vertically installed outside the process tube **203**. The boat elevator is configured to move the seal cap **219** vertically for loading/unloading the boat **217** to/from the process chamber **201**.

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The boat **217** is made of a heat-resistant material such as quartz or silicon carbide and is configured to support a plurality of wafers **200** in a state where the wafers **200** are horizontally oriented and arranged in multiple stages with the centers of the wafers **200** being aligned with each other. In addition, at the lower part of the boat **217**, an insulating member **218** made of a heat-resistant material such as quartz or silicon carbide is installed so as to prevent heat transfer from the heater **207** to the seal cap **219**. The insulating member **218** may include a plurality of insulating plates made of a heat-resistant material such as quartz or silicon carbide, and an insulating plate holder configured to support the insulating plates in a state where the insulating plates are horizontally oriented and arranged in multiple stages. Inside the process tube **203**, a temperature sensor **263** is installed as a temperature detector, and by controlling power supplied to the heater **207** based on temperature information detected by the temperature sensor **263**, desired temperature distribution can be attained at the inside of the process chamber **201**. Like the first nozzle **233a** and the second nozzle **233b**, the temperature sensor **263** is installed along the inner wall of the process tube **203**.

A controller **280** which is a control unit (control device) is connected to the first to fourth MFC **241a**, **241b**, **302**, and **352**, the first to fourth valves **243a**, **243b**, **304**, and **305**, the pressure sensor **245**, the APC valve **242**, the heater **207**, the temperature sensor **263**, the vacuum pump **246**, the rotary mechanism **267**, and so on.

The controller **280** is used to control, for example, flowrates of the first to fourth MFC **241a**, **241b**, **302**, and **352**; opening/closing operations of the first to fourth valves **243a**, **243b**, **304**, and **305**; opening/closing operations of the APC valve **242** and pressure adjusting operations of the APC valve **242** based on the pressure sensor **245**; the temperature of the heater **207** based on the temperature sensor **263**; starting/stopping operations of the vacuum pump **246**; and the rotation speed of the rotary mechanism **267**.

(2) Method of Forming Silicon Nitride Film

Next, as an example of a film-forming method for a semiconductor device manufacturing process using the above-described substrate processing apparatus, an exemplary method of forming a silicon nitride (SiN) film containing stoichiometrically excessive silicon (Si) with respect to nitrogen (N) (i.e., a silicon-rich silicon nitride film) by using dichlorosilane (DCS) and ammonia (NH_3) will now be described according to an embodiment. In addition, the present invention can be applied to any kind of film without being limited to a silicon-rich silicon nitride film so long as the film is formed by using two or more kinds of gases.

In the following description, components of the substrate processing apparatus are controlled by the controller **280**.

In the current embodiment, a film is formed by using a method similar to but not identical to an atomic layer deposition (ALD) method. In an ALD method, process gases which provide at least two source materials for forming a film are supplied to a substrate in turns under predetermined film forming conditions (temperature, time, etc.), so as to allow the process gases to be adsorbed on the substrate on an atomic layer basis for forming a film by surface reaction. At this time, the thickness of the film can be controlled by adjusting the number of process gas supply cycles (for example, if the film forming rate is 1 Å/cycle and it is intended to form a 20-Å film, the process is repeated 20 cycles).

That is, in the film-forming method of the current embodiment, a process of supplying DCS to a wafer **200** under

conditions where chemical vapor deposition (CVD) reaction is caused, and a process of supplying NH_3 to the wafer **200** under a non-plasma condition and other predetermined conditions are repeated in turns so as to form a silicon-rich silicon nitride (SiN). In the current embodiment, a process (Step 1) of supplying DCS to a wafer **200**, a process (Step 2) of removing the DCS from the wafer **200**, a process (Step 3) of supplying NH_3 to the wafer **200**, and a process (Step 4) of removing the NH_3 from the wafer **200** are set to one cycle, and the cycle is repeated a plurality of times to form a silicon-rich silicon nitride (SiN) film. In the process (Step 1) of supplying DCS to a wafer **200**, a silicon film having several or less atomic layers (1/n to several atomic layers) is formed on the wafer **200**. At this time, an excessive amount of silicon (Si) is supplied. Furthermore, in the process (Step 3) of supplying NH_3 to the wafer **200**, the silicon film having several or less atomic layers and formed on the wafer **200** is thermally nitrided. At this time, the silicon film is nitrided by NH_3 in a non-saturated condition. That is, the silicon film is not completely nitrided, and thus Si—N bonds are not fully made. In this way, nitriding of silicon (Si) is suppressed, and thus silicon (Si) becomes surplus. At this time, to obtain a condition where nitriding of the silicon film is not saturated, it is preferable that at least one of the supply flowrate of NH_3 , the supply time of NH_3 , and the inside pressure of the process chamber **201** be adjusted to be different from a condition where the nitriding of the silicon film is saturated. That is, as compared with a condition where nitriding of the silicon film is saturated, the supply flowrate of NH_3 is reduced, the supply time of NH_3 is shortened, or the inside pressure of the process chamber **201** is reduced. For example, a small amount of NH_3 is supplied as compared with the amount of NH_3 necessary for forming a silicon nitride (Si_3N_4) film having a stoichiometric composition. As described above, the supply flowrate of silicon (Si) is controlled in the process of forming a silicon film having several or less atomic layers on a wafer **200** by using a CVD method, and the nitriding degree of silicon (Si) is controlled in the process of thermally nitriding the silicon film with NH_3 . The processes are alternately repeated to form a silicon-rich silicon nitride (SiN) film while controlling the Si/N composition ratio of the silicon nitride (SiN).

Hereinafter, the film-forming method of the current embodiment will be described in detail with reference to FIG. 3.

After a plurality of wafers **200** are charged into the boat **217** (wafer charging), as shown in FIG. 1, the boat **217** in which the plurality of wafers **200** are charged is lifted and loaded into the process chamber **201** by the boat elevator (not shown) (boat loading). In this state, the bottom side of the process tube **203** is sealed by the seal cap **219** with the O-ring **220b** being disposed therebetween.

The inside of the process chamber **201** is vacuum-evacuated to a desired pressure (vacuum degree) by using the vacuum pump **246**. At this time, the pressure inside the process chamber **201** is measured by the pressure sensor **245**, and based on the measured pressure, the APC valve **242** is feedback-controlled (pressure adjustment). In addition, the inside of the process chamber **201** is heated to a desired temperature by using the heater **207**. At this time, to obtain desired temperature distribution inside the process chamber **201**, power to the heater **207** is feedback-controlled based on temperature information measured by the temperature sensor **263** (temperature adjustment). Next, the boat **217** is rotated by the rotary mechanism **267** to rotate the wafers **200**. Thereafter, the following four steps are sequentially performed.

(Step 1)

The first valve **243a** of the first gas supply pipe **232a** is opened to allow DCS to flow through the first gas supply pipe **232a**. At this time, inert gas may be allowed to flow through the first gas supply pipe **232a**. The flowrate of DCS flowing through the first gas supply pipe **232a** is controlled by the first MFC **241a**, and the DCS is mixed with flowrate-controlled inert gas. Then, the mixture is supplied to the inside of the process chamber **201** through the first gas supply holes **248a** of the first nozzle **233a** and is discharged through the gas exhaust pipe **231**. At this time, the APC valve **242** is properly controlled to keep the inside of the process chamber **201** at a pressure of 133 Pa to 1333 Pa, for example, 133 Pa. The first MFC **241a** is used to adjust the flowrate of DCS in the range from 0.1 slm to 10 slm, for example, 0.5 slm. The wafers **200** are exposed to DCS, for example, for 1 second to 180 seconds. At this time, the heater **207** is controlled to allow thermal decomposition of DCS for inducing CVD reaction. That is, the heater **207** is controlled to heat the wafers **200** to a temperature of 550° C. to 700° C., for example, 630° C. By supplying DCS to the inside of the process chamber **201** under the above-described conditions, silicon (Si) films each including several or less atomic layers (that is, 1/n atomic layer to several atomic layers) are formed on the wafers **200** (deposition of CVD-Si film). For example, silicon films each including a half atomic layer (half layer) or a mono atomic layer (mono layer) may be formed. In this way, silicon (Si) is excessively supplied.

(Step 2)

After the silicon films each including several or less atomic layers are formed, the first valve **243a** of the first gas supply pipe **232a** is closed so as to interrupt supply of DCS. At this time, in a state where the APC valve **242** of the gas exhaust pipe **231** is opened, the inside of the process chamber **201** is vacuum-exhausted to 10 Pa or less by using the vacuum pump **246** to remove remaining DCS from the inside of the process chamber **201**. Along with this, if inert gas such as N_2 is supplied to the inside of the process chamber **201**, the remaining DCS may be removed more efficiently (remaining gas removal).

(Step 3)

The second valve **243b** of the second gas supply pipe **232b** is opened to allow NH_3 to flow through the second gas supply pipe **232b**. At this time, inert gas may be allowed to flow through the second gas supply pipe **232b**. The flowrate of NH_3 flowing through the second gas supply pipe **232b** is controlled by the second MFC **241b**, and the NH_3 is mixed with flowrate-controlled inert gas. Then, the mixture is supplied to the inside of the process chamber **201** through the second gas supply holes **248b** of the second nozzle **233b** and is discharged through the gas exhaust pipe **231**. As described above, NH_3 is supplied to the inside of the process chamber **201** in a state where the NH_3 is not activated by plasma.

In Step 3, the inside conditions of the process chamber **201** are adjusted so that the silicon films are nitrided under conditions where the nitriding reaction of the silicon film by the NH_3 is not saturated. That is, the supply amount of NH_3 is adjusted to be less than an amount necessary for nitriding the silicon films to form silicon nitride (Si_3N_4) films each having a stoichiometric composition. In addition, at this time, the APC valve **242** is properly adjusted to keep the inside of the process chamber **201** at a pressure of 133 Pa to 1333 Pa, for example, 865 Pa. The second MFC **241b** is controlled to supply NH_3 at a flowrate of 0.1 slm to 10 slm, for example, 1 slm. The wafers **200** are exposed to NH_3 for 1 second to 180 seconds. At this time, the heater **207** is controlled so as to keep the wafers **200** in the same temperature range of 550° C. to

700° C., for example, 630° C., like the case of supplying DCS in Step 1. In this way, NH₃ is supplied to the inside of the process chamber **201** in a non-plasma condition, so as to thermally nitride the silicon films each including several or less atomic layers and formed on the wafers **200** (thermal nitriding of CVD-Si film). At this time, since silicon is excessive due to the restrained nitriding of silicon (Si), silicon-rich silicon nitride films can be formed.

If it is assumed that all DCS and NH₃ supplied to the inside of the process chamber **201** are used to form a silicon nitride film, a silicon nitride (Si₃N₄) film having a stoichiometric composition can be formed on a wafer **200** by supplying DCS which is a silicon-containing substance and NH₃ which is a nitrogen-containing substance to the inside of the process chamber **201** at a ratio of 3:4. In the current embodiment, however, the supply amount of NH₃ is less than the amount necessary for thermally nitriding a silicon film to form a silicon nitride (Si₃N₄) film having a stoichiometric composition. That is, the supply amount of NH₃ is restricted so as not to saturate nitriding reaction of the silicon film. In this way, the amount of nitrogen is adjusted to be insufficient for forming a silicon nitride (Si₃N₄) film having a stoichiometric composition, so that a silicon-rich silicon nitride film can be formed on the wafer **200**.

Practically, the composition ratio of silicon/nitrogen of a silicon nitride film is varied not only by the supply amount of NH₃, but also by other conditions in Step 3, such as difference of reactivity caused by the inside pressure of the process chamber **201**, difference of reactivity caused by the temperature of a wafer **200**, the supply flowrate of NH₃, and the supply time of NH₃ (that is, reaction time). In addition, the composition ratio of silicon and nitrogen of a silicon nitride film is also varied by conditions in Step 1, such as the pressure inside the process chamber **201**, the temperature of a wafer **200**, the supply flowrate of DCS, and the supply time of DCS. That is, controlling of the balance between the supply of silicon (Si) in Step 1 and the supply of nitrogen (N) in Step 3 is important for controlling the composition ratio of silicon and nitrogen (Si/N ratio) of a silicon nitride film. In the current embodiment, the pressure inside the process chamber **201**, the temperature of a wafer **200**, the supply flowrate of gas, and the supply time of gas are properly controlled within the above-described mentioned ranges, so as to control the composition ratio of silicon/nitrogen of a silicon nitride film. If the amount of silicon (Si) supplied in Step 1 is concerned as a reference (is fixed to a predetermined value), the Si/N ratio is most dependent on the supply flowrate of NH₃, the supply time of NH₃, and the pressure inside the process chamber **201** among conditions in Step 3. Therefore, in Step 3, it is preferable that at least one of the supply flowrate of NH₃, the supply time of NH₃, and the pressure inside the process chamber **201** be different from conditions where the nitriding reaction of a silicon film is saturated. Specifically, the supply flowrate of NH₃, the supply time of NH₃, or the pressure inside the process chamber **201** may be reduced as compared with a condition where the nitriding reaction of a silicon film is saturated.

(Step 4)

After the silicon films each including several or less atomic layers are thermally nitrided, the second valve **243b** of the second gas supply pipe **232b** is closed to interrupt supply of NH₃. At this time, in a state where the APC valve **242** of the gas exhaust pipe **231** is opened, the inside of the process chamber **201** is exhausted to a pressure of 10 Pa or less to remove remaining NH₃ from the inside of the process chamber **201**. Along with this, if inert gas such as N₂ is supplied to

the inside of the process chamber **201**, remaining NH₃ can be removed more efficiently (remaining gas removal).

By setting the above-mentioned Steps 1 to 4 to one cycle, and repeating this cycle a plurality of times, silicon-rich silicon nitride films can be formed on the wafers **200** to a predetermined thickness.

After silicon-rich silicon nitride films are formed to a predetermined thickness, the inside of the process chamber **201** is purged by supplying inert gas such as N₂ to the inside of the process chamber **201** and exhausting the inert gas from the inside of the process chamber **201** (purge). By this, the inside atmosphere of the process chamber **201** is replaced with inert gas, and the inside pressure of the process chamber **201** is returned to atmospheric pressure (returning to atmospheric pressure).

Thereafter, the seal cap **219** is moved downward by the boat elevator (not shown) so as to open the bottom side of the process tube **203** and unload the processed wafers **200** from the inside of the process tube **203** through the bottom side of the process tube **203** in a state where the processed wafers **200** are held in the boat **217** (boat unloading). Then, the processed wafers **200** are discharged from the boat **217** (wafer discharging).

Although DCS is used as a silicon source in the above description, the present invention is not limited thereto. For example, another substance such as trichlorosilane (SiHCl₃, abbreviation: TCS), hexachlorosilane (Si₂Cl₆, abbreviation: HCD), monosilane (SiH₄), and disilane (Si₂H₆) may be used.

(3) Cleaning Method

After a process of forming a silicon-rich silicon nitride is performed predetermined times, a cleaning process is performed on the process chamber **201** by using a cleaning gas. In the current embodiment, for example, chlorine trifluoride (ClF₃) is used as a cleaning gas.

The first nozzle **233a** and the inside of the process tube **203** (for example, the inner wall of the process tube **203**, the outer walls of the first nozzle **233a** and the second nozzle **233b**, and the boat **217**) are cleaned under conditions optimal for the respective parts.

<Method of Cleaning Inner Wall of First Nozzle>

First, cleaning of the inner wall of the first nozzle **233a** will be explained (FIG. 4). Cleaning of the inner wall of the first nozzle **233a** is performed under a pressure lower than a pressure at which the inside of the process tube **203** is cleaned.

(Step 11)

In Step 11, first, the APC valve **242** is opened to exhaust the inside of the process chamber **201**. At this time, the fourth valve **354** and the first valve **243a** are closed.

(Step 12)

If the inside of the process chamber **201** is sufficiently exhausted, the fourth valve **354** is opened to supply ClF₃ gas to the first nozzle **233a** while controlling the flowrate of the ClF₃ gas by using the fourth MFC **352** (Step 12). At this time, the flowrate of the ClF₃ gas is set to from 0.1 slm to 0.4 slm, for example, 0.1 slm. In addition, inert gas such as N₂ gas is simultaneously supplied, for example, at a flowrate of 0.4 slm, and the ClF₃ concentration of the inside of the first nozzle **233a** is set to from 20% to 50%, for example, 20%. In the case where the ClF₃ concentration of the inside of the first nozzle **233a** is kept higher than 20%, the flowrate of N₂ gas simultaneously supplied through a part such as the second nozzle **233b** is increased so as to keep the concentration of ClF₃ equal to or lower than 20% when the ClF₃ is exhausted from the inside of the process chamber **201**.

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Furthermore, in a state where the APC valve **242** is opened, the controller **280** adjusts pressure to a predetermined level. Preferably, the pressure is adjusted to a constant level between 10 Pa to 400 Pa, for example, 66.7 Pa (0.5 Torr). By this, a silicon film (unnecessary silicon film to be removed), which is accumulated on the inner wall of the first nozzle **233a** during the above-described film-forming process, is brought into reaction with supplied ClF_3 gas.

(Step 13)

After ClF_3 gas is supplied to the first nozzle **233a** for a predetermined time, the first valve **243a** is closed, and the inside of the process chamber **201** is exhausted (Step 13). In addition, while ClF_3 is supplied through the first nozzle **233a**, inert gas such as N_2 gas may be supplied to the inside of the process chamber **201** through the second nozzle **233b** and the short pipe **301**. By supplying inert gas such as N_2 gas, reverse flows of ClF_3 gas from the inside of the process chamber **201** to the second nozzle **233b** and the short pipe **301** can be prevented.

<Method of Cleaning Inside of Process Tube>

Next, a method of cleaning the inside of the process tube **203** will be explained.

The following two steps are mainly performed (FIG. 5).

(Step 21)

In Step 21, the process chamber **201** is filled with ClF_3 gas. First, the temperature of the heater **207** is set to from 400° C. to 420° C., for example, 400° C. Then, in a state where the inside of the process chamber **201** is exhausted by opening the APC valve **242** (the fourth valve **354** is closed), the third valve **304** is opened to supply ClF_3 to the first cleaning gas supply pipe **300** and fully fill the inside of the process chamber **201** with the ClF_3 . For example, the flowrate of ClF_3 supplied through the short pipe **301** is set to 0.5 slm. Since parts such as an exhaust pipe may be corroded if the concentration of ClF_3 is high, the concentration of ClF_3 is set to, for example, 20%. To control the inside pressure of the process chamber **201**, the APC valve **242** is opened, and the inside pressure of the process chamber **201** is adjusted to a predetermined level. Preferably, the inside pressure of the process chamber **201** is adjusted to a constant level between 400 Pa to 1000 Pa, for example, 931 Pa (7 Torr).

By supplying ClF_3 to the inside of the process chamber **201** through the short pipe **301** as described above, the inside of the process chamber **201** can be cleaned without involving the first nozzle **233a**.

In addition, inert gas such as N_2 gas may be supplied through the first nozzle **233a** and the second nozzle **233b**. By supplying N_2 gas, reverse flows of ClF_3 gas from the inside of the process chamber **201** to the first nozzle **233a** and the second nozzle **233b** can be prevented. The flowrate of N_2 gas supplied through the first nozzle **233a** and the second nozzle **233b** may be 0.8 slm, for example. Furthermore, inert gas such as N_2 gas may be supplied through the rotation shaft (not shown) of the rotary mechanism **267**, for example, at a flowrate of 0.3 slm.

Then, if a predetermined time (for example, 85 seconds) elapses after the third valve **304** is opened, Step 22 is performed.

(Step 22)

In Step 22, gas filled in the process chamber **201** is exhausted. A silicon nitride film (unnecessary silicon nitride film to be removed) accumulated in the process chamber **201** during the film-forming process is brought into reaction with ClF_3 supplied in Step 21, and ClF_3 gas (including ClF_3 gas not participated in reaction) and N_2 gas are mainly filled in the process chamber **201**. Therefore, such gases are exhausted from the process chamber **201**.

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In detail, the APC valve **242** is opened so as to exhaust gas filled in the process chamber **201** at a time through the gas exhaust pipe **231**.

Then, if a predetermined time (for example, 10 seconds) after the APC valve **242** is opened, Step 22 is stopped. Thereafter, Step 21 and Step 22 are set as a cycle, and the cycle is repeated predetermined times. In this way, cleaning of the inside of the process tube **203** is completed.

Furthermore, in Step 22, at the same time with vacuum evacuation, N_2 purge may be performed by supplying inert gas such as N_2 through the first nozzle **233a**, the second nozzle **233b**, and the short pipe **301**; or in Step 22, vacuum evacuation and N_2 purge may be alternately repeated predetermined times.

By repeating Step 21 and Step 22 (one cycle) predetermined times, the inside of the process tube **203** is cleaned. As described above, exhaustion of gas that does not contribute to cleaning, and supply of new ClF_3 gas are repeated, so that cleaning gas can be effectively reacted with a silicon nitride accumulated in the inside of the process tube **203**.

Either the cleaning of the inner wall of the first nozzle **233a** or the cleaning of the inside of the process tube **203** may first be performed, and then the other may be performed; however, it is preferable that the cleaning of the inner wall of the first nozzle **233a** be first performed. In the case where the cleaning of the inner wall of the first nozzle **233a** is first performed, ClF_3 gas that passes through the first nozzle **233a** with reaction is supplied to the inside of the process tube **203**, and the ClF_3 gas reacts with a silicon nitride film accumulated in the inside (inner wall, etc.) of the process tube **203**, so that the silicon nitride film can be removed. Therefore, if the cleaning of the inside of the process tube **203** is performed after the cleaning of the inner wall of the first nozzle **233a**, time necessary for cleaning the inside of the process tube **203** can be reduced. That is, by cleaning the inner wall of the first nozzle **233a** first, a high etching rate can be obtained, and thus throughput can be improved.

In addition, since a silicon nitride film is attached to almost all the region of the inside of the process tube **203**, the cleaning cycle may be determined according to the thickness of the silicon nitride film accumulated in the process tube **203** (corresponding to the amount of deposition on a wafer), and the cleaning cycle may be performed each time after the film-forming process is repeated a predetermined number of times. Therefore, cleaning conditions of the inside of the process tube **203** such as the inside pressure of the process tube **203** or the supply flowrate of cleaning gas may be determined according to the actual amount of deposition. The amount of deposition on wafers can be calculated by monitoring the supply flowrate of NH_3 .

Meanwhile, the thickness of a silicon film accumulated on the inner wall of the first nozzle **233a** is varied according to film-forming conditions such as substrate temperature, DCS supply time, and DCS supply amount. Therefore, cleaning conditions of the inner wall of the first nozzle **233a** such as the inside pressure of the first nozzle **233a** and the supply flowrate of cleaning gas are determined according to film-forming conditions such as DCS supply time and DCS supply flowrate. The cleaning cycle of the inside of the first nozzle **233a** is determined according to film-forming conditions such as DCS supply time and DCS supply flowrate. In addition, when DCS is supplied as a process gas, the thickness of a silicon film accumulated on the inner wall of the first nozzle **233a** may be proportional to the supply amount of silicon molecules.

As described above, for removing the thickness of a film by a desired amount, that is, for removing the accumulated thick-

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ness of a film by a desired amount, cleaning conditions of the inside of the process tube **203** are adjusted according to the number of cycles of the silicon nitride film forming process, and cleaning conditions of the inner wall of the first nozzle **233a** are adjusted according to film-forming conditions such as DCS supply time and DCS supply flowrate.

In addition, preferably, the cleaning conditions and cleaning timing of the insides of the first nozzle **233a** and the process tube **203** may be determined and controlled by control units **500a** and **500b** as shown in FIG. 7A and FIG. 7B.

FIG. 7A illustrates the control unit **500a** configured to control cleaning conditions and timing of the first nozzle **233a** by monitoring film-forming conditions when DCS is supplied. That is, each time a film-forming process is performed, the supply amount of DCS is monitored by a monitoring unit **510a** which is configured to monitor the first MFC **241a** which is a flowrate controller (flowrate control unit) or to monitor a process recipe (film-forming process conditions), and the monitored supply amount of DCS is added by a counter such as an adding unit **520a**. The added DCS supply amount (the accumulated amount of DCS) is stored in a memory device such as a memory unit **530a**. The accumulated amount of DCS is compared with a predetermined threshold value by a comparison unit **540a**. The threshold value is preset at the comparison unit **540a**.

If the accumulated amount of DCS reaches the threshold value, the comparison unit **540a** informs a signal output unit **550a** of the event, and then the signal output unit **550a** sends at least one of a cleaning condition setting signal and a cleaning start signal to the controller **280**.

Similarly, FIG. 7B illustrates the control unit **500b** configured to control cleaning conditions and timing of the second nozzle **233b** by monitoring film-forming conditions when NH_3 is supplied through the second nozzle **233b**. That is, each time a film-forming process is performed, the supply amount of NH_3 is monitored by a monitoring unit **510b** which is configured to monitor the second MFC **241b** which is a flowrate controller (flowrate control unit) or to monitor a process recipe (film-forming process conditions), and the monitored supply amount of NH_3 is added by a counter such as an adding unit **520b**. The added NH_3 supply amount (the accumulated amount of NH_3) is stored in a memory device such as a memory unit **530b**. The accumulated amount of NH_3 is compared with a predetermined threshold value by a comparison unit **540b**. The threshold value is preset at the comparison unit **540b**.

If the accumulated amount of NH_3 reaches the threshold value, the comparison unit **540b** informs a signal output unit **550b** of the event, and then the signal output unit **550b** sends at least one of a cleaning condition setting signal and a cleaning start signal to the controller **280**.

In addition, after considering things related to cleaning quality, such as whether a desired film is uniformly removed (without over-etching of quartz), whether corrosion occurs, whether contaminants generate, and whether remaining gas affects a film-forming process, cleaning conditions and timing are determined to increase the etching rate (that is, throughput).

Furthermore, when the inside of the process tube **203** is cleaned, inert gas is continuously supplied to the first nozzle **233a** and the second nozzle **233b**.

Furthermore, cleaning of the inside of the process tube **203** may be overlapped with cleaning of the inner wall of the first nozzle **233a** at least partially. In this case, if the cleaning of the inner wall of the first nozzle **233a** is performed at the same pressure as a pressure at which the cleaning of the inside of the process tube **203** is performed, the first nozzle **233a** may

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be damaged and broken. On other hand, if the cleaning of the inside of the process tube **203** is performed at the same pressure as a pressure at which the cleaning of the inner wall of the first nozzle **233a** is performed, the cleaning time may be increased because the pressure is too low. For this reason, although the cleaning of the inner wall of the first nozzle **233a** is performed at the same pressure as a pressure at which the cleaning of the inside of the process tube **203** is performed, a low-concentration cleaning gas is supplied to the inner wall of the first nozzle **233a**. Since a cleaning gas is supplied only through the short pipe **301** during a cleaning process of the inside of the process tube **203** and a cleaning gas is supplied only to the first nozzle **233a** during a cleaning process of the inner wall of the first nozzle **233a**, flowrate tuning is necessary for performing the two cleaning processes at the same time.

In addition, if the amount of silicon attached to the inner wall of the first nozzle **233a** is large, since it is difficult to remove the silicon from the first nozzle **233a**, the pressure of a cleaning process is increased. However, if the pressure is increased too much, although the cleaning process can be completed more rapidly owing to an increased etching rate, the first nozzle **233a** may be devitrified due to generation of heat. If the first nozzle **233a** is damaged in this way, it may be necessary to replace the first nozzle **233a**. In addition, since the inside of the first nozzle **233a** is narrow and long, by rapidly making the inside pressure of the first nozzle **233a** uniform, the rate of etching can be made uniform in the vertical direction.

According to the current embodiment, one or more of the following effects can be attained.

The inside of the process tube **203**, where a silicon nitride is accumulated, and the inner wall of the first nozzle **233a**, where a silicon source such as DCS is supplied and a silicon film is accumulated, are cleaned under conditions optimized for the respective parts, so that cleaning can be efficiently performed with less contamination, damage of the process tube **203**, and damage of the first nozzle **233a**.

That is, cleaning can be thoroughly performed with less cleaning time and good gas consumption efficiency without a remaining film.

In addition, generation of contamination caused by excessive etching conditions can be reduced; operational costs can be reduced because the process tube **203** and the first nozzle **233a** can be less damaged; and maintenance time can be reduced.

When a silicon nitride film attached to the inside of the process tube **203** is cleaned, by filling a high-concentration cleaning gas in the entire inside of the process tube **203** and increasing the inside pressure of the process tube **203**, particularly, the upper part of the process chamber **201** can be less affected by gas flow distribution, and the cleaning process can be completed within a shorter time.

When a silicon nitride film attached to the inside of the process tube **203** is cleaned, by alternately repeating supply of a cleaning gas and exhaustion of the cleaning gas (cyclic supply), stagnant gas can be exhausted by distribution of gas flows and thus be replaced with a cleaning gas. That is, exhaustion of gas that has reacted with a silicon nitride film accumulated on the inside of the process tube **203** (that is, exhaustion of gas that does not contribute to cleaning anymore), and introduction of a new cleaning gas are repeated, so that cleaning can be effectively performed with a shorter time and less consumption of cleaning gas.

When cleaning a silicon film attached to the inner wall of the first nozzle **233a** which is used to supply a silicon source such as DCS, pressure is kept lower than a pressure at which

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the inside of the process tube **203** is cleaned, so as to weaken cleaning reaction power for preventing damage of a quartz part. In addition, if reaction power is high, heat generation may increase to cause breakage of a quartz part, and if reaction speed is high, a silicon film may decompose destructively to cause contamination. That is, these disadvantages can be prevented.

When cleaning a silicon film attached to the inner wall of the first nozzle **233a** which is used to supply a silicon source such as DCS, supply and exhaustion of a cleaning gas are continuously performed instead of alternately repeating them, so that gas participated in reaction and not participated in reaction can be efficiently discharged and the cleaning process can be rapidly completed.

(4) Another Embodiment

According to another embodiment, a method of cleaning the process tube **203** will now be described with reference to FIG. 6 and FIG. 8. The same elements as those shown in FIG. 1 will be denoted by the same reference numerals, and descriptions thereof will not be repeated.

At a first cleaning gas supply pipe **300**, a gas reservoir **306** and an on-off valve such as a fifth valve **308** are installed as well as a flowrate control device such as a third MFC **302** and an on-off valve such as a third valve **304**, and the fifth valve **308** is configured to be controlled by a controller **280**.

(Step 31)

First, ClF_3 gas is filled in a process chamber **201** as follows: in a state where the inside of the process chamber **201** is exhausted by opening an APC valve **242** (a fourth valve **354** is closed), the third valve **304** is opened and the fifth valve **308** is closed so as to introduce ClF_3 gas into the first cleaning gas supply pipe **300** and store the ClF_3 gas in the gas reservoir **306** while controlling the flowrate of the ClF_3 using the third MFC **302** (Step 31).

(Step 32)

If a predetermined amount of ClF_3 gas is stored in the gas reservoir **306**, the third valve **304** is closed to stop an inflow of ClF_3 gas into the gas reservoir **306**. In this state, the ClF_3 gas stored in the gas reservoir **306** is supplied to the process chamber **201** at a time (a flash flow) by opening the fifth valve **308** so as to fill the inside of the process chamber **201** with the ClF_3 gas. In addition, the APC valve **242** is opened to control the inside pressure of the process chamber **201** to a predetermined level (Step 32).

(Step 33)

Like the case where the gas reservoir **306** is not used, gas filled in the process chamber **201** is exhausted (Step 33). After a predetermined time from the opening of the APC valve **242**, the process of Step 33 is completed.

After that, Step 31, Step 32, and Step 33 are set as one cycle, and this cycle is repeated predetermined times. In this way, cleaning of the inside of the process tube **203** is completed.

While the process of Step 32 is performed, Step 31 may be concurrently performed to store ClF_3 gas in the gas reservoir **306** (that is, the third valve **304** is opened and the fifth valve **308** is closed to store ClF_3 gas in the gas reservoir **306**). In this case, the process time of the entire cleaning process can be reduced. Furthermore, without Step 31 for storing ClF_3 gas in the gas reservoir **306**, ClF_3 gas may be supplied to the inside of the process chamber **201** and filled in the inside of the process chamber **201** only by manipulating each valve.

As described above, when a silicon nitride film attached to the inside of the process tube **203** is cleaned, a cleaning gas is instantaneously supplied to the inside of the process tube **203**

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to increase the gas concentration of the inside of the process tube **203** and fill the cleaning gas in the entire inside of the process tube **203**. By increasing pressure in this way, particularly, the effect of gas flow distribution in the upper region of the process chamber **201** can be reduced, and cleaning can be performed within a shorter time.

In addition, since the temperature of the lower side of the process tube **203** is lower than temperature of the upper side of the process tube **203**, it is more difficult to remove a silicon nitride film attached to the lower side of the process tube **203**. Therefore, a cleaning process may be divided into a process of cleaning the entire inside of the process tube **203** and a process of cleaning the lower side of the process tube **203**, and the process of cleaning the entire inside of the process tube **203** may be performed at a high pressure (high-pressure cycle) but the process of cleaning the lower side of the process tube **203** may be performed at a relatively low pressure (low-pressure cycle). In the case of the low-pressure process, it is preferable that a cleaning gas be continuously supplied instead of supplying the cleaning gas instantaneously. In this way, the cleaning process of the inside of the process tube **203** may be performed in two cleaning steps: a high-pressure intermittent cleaning step and a low-pressure continuous cleaning step. Alternatively, in a way of varying pressure when a cleaning gas is supplied, silicon nitride films attached to the upper and lower sides of the process tube **203** may be preferentially removed.

In the above described description, a silicon-rich silicon nitride film is described as a film to be formed on a substrate; however, the present invention is not limited thereto. For example, the present invention can be applied to apparatuses configured to form films such as a silicon nitride film having a stoichiometric composition ratio, an aluminum nitride film, a titanium nitride film, a hafnium nitride film, a zirconium nitride film, a silicon oxide film, a silicon oxynitride film, an aluminum oxide film, a titanium oxide film, a hafnium oxide film, a zirconium oxide film, and a silicon oxide film. That is, the present invention can be applied to an apparatus in which different kinds of films are formed on the inside of a process tube and the inner wall of a gas supply nozzle (i.e., an apparatus including gas supply nozzles for respective process gases).

In addition, besides a silicon (Si)-containing gas, a metal element-containing gas such as an aluminum (Al)-containing gas, a titanium (Ti)-containing gas, a hafnium (Hf)-containing gas, and a zirconium (Zr)-containing gas may be used as a process gas capable of depositing a film by itself at a certain temperature, and besides a nitrogen (N)-containing gas, gas such as an oxygen (O)-containing gas may be used as a process gas incapable of depositing a film by itself at a certain temperature.

Furthermore, although chlorine trifluoride (ClF_3) is described as an example of a cleaning gas, the present invention is not limited thereto. For example, gas including at least one gas selected from the group consisting of nitrogen trifluoride (NF_3) gas, fluorine (F_2) gas, hydrogen fluoride (HF) gas, chlorine (Cl_2) gas, and boron trichloride (BCl_3) gas may be used as a cleaning gas.

According to the method of manufacturing a semiconductor device, the cleaning method, and the substrate processing apparatus of the present invention, the reaction tube and the gas supply nozzle can be cleaned under conditions optimized according to the film-forming conditions of the reaction tube and the gas supply nozzle, thereby making it possible to perform a cleaning process with less contamination and damages on the reaction tube and the gas supply nozzle.

<Supplementary Note>

The present invention also includes the following preferred embodiments.

(Supplementary Note 1)

According to an embodiment of the present invention, there is provided a method of manufacturing a semiconductor device, the method comprising: loading a substrate into a process chamber; forming a film on the substrate by supplying a first process gas, which comprises at least one of a plurality of elements constituting the film and is capable of depositing a film by itself, to an inside of the process chamber through a first gas introducing part, and supplying a second process gas, which comprises at least one of the others of the plurality of elements constituting the film and is incapable of depositing a film by itself, to the inside of the process chamber through a second gas introducing part; unloading the substrate from the process chamber after the film is formed on the substrate; performing a first cleaning process so as to remove a first deposition substance attached to an inner wall of the first gas introducing part by supplying a cleaning gas to the first gas introducing part; and performing a second cleaning process so as to remove a second deposition substance attached to the inside of the process chamber and having a chemical composition different from that of the first deposition substance by supplying a cleaning gas to the inside of the process chamber through a third gas introducing part connected to a lower side of the process chamber at a position where the substrate is not placed, wherein in the performing of the first cleaning process, cleaning conditions are set according to accumulated supply time of the first process gas supplied to the inside of the process chamber through the first gas introducing part, and in the performing of the second cleaning process, cleaning conditions are set according to an accumulated thickness of the film formed on the substrate.

(Supplementary Note 2)

Preferably, the cleaning conditions may be a pressure of the inside of the process chamber and a flowrate of the cleaning gas.

(Supplementary Note 3)

Preferably, a pressure of the inside of the process chamber in the first cleaning process may be set to be lower than a pressure of the inside of the process chamber in the second cleaning process.

(Supplementary Note 4)

Preferably, the first deposition substance may comprise at least one of the plurality of elements as a main component, and the second deposition substance may comprise the plurality of elements as main components.

(Supplementary Note 5)

Preferably, the first process gas may be a silicon-containing gas, and the second process gas may be a nitrogen-containing gas.

(Supplementary Note 6)

Preferably, the cleaning gas may comprise at least one selected from the group consisting of nitrogen trifluoride (NF_3) gas, chlorine trifluoride (ClF_3) gas, fluorine (F_2) gas, hydrogen fluoride (HF) gas, chlorine (Cl_2) gas, and boron trichloride (BCl_3) gas.

(Supplementary Note 7)

Preferably, in the first cleaning process, the cleaning gas may be continuously supplied to the first gas introducing part, and in the second cleaning process, the cleaning gas may be intermittently supplied to the inside of the process chamber.

(Supplementary Note 8)

According to another embodiment of the present invention, there is provided a cleaning method for removing a film attached to an inside of a process chamber of a substrate

processing apparatus which is used to form a film on a substrate by supplying a process gas to the substrate, the cleaning method comprising: setting pressure of the inside of the process chamber to a first pressure and intermittently supplying a cleaning gas to the inside of the process chamber; and setting the pressure of the inside of the process chamber to a second pressure higher than the first pressure and continuously supplying the cleaning gas to the inside of the process chamber.

(Supplementary Note 9)

According to another embodiment of the present invention, there is provided a method of manufacturing a semiconductor device, the method comprising: loading a substrate into a process chamber; forming a film on the substrate by supplying a first process gas, which comprises at least one of a plurality of elements constituting the film and is capable of depositing a film by itself, to an inside of the process chamber through a first gas introducing part, and supplying a second process gas, which comprises at least one of the others of the plurality of elements constituting the film and is incapable of depositing a film by itself, to the inside of the process chamber through a second gas introducing part; unloading the substrate from the process chamber after the film is formed on the substrate; performing a first cleaning process so as to remove a first deposition substance attached to an inner wall of the first gas introducing part by supplying a cleaning gas to the first gas introducing part; and performing a second cleaning process so as to remove a second deposition substance attached to the inside of the process chamber and having a chemical composition different from that of the first deposition substance by supplying a cleaning gas to the inside of the process chamber through a third gas introducing part connected to a lower side of the process chamber at a position where the substrate is not placed, wherein when at least parts of the first cleaning process and the second cleaning process are simultaneously performed, concentration of the cleaning gas supplied to the first gas introducing part is lower than concentration of the cleaning gas supplied through the third gas introducing part.

(Supplementary Note 10)

According to another embodiment of the present invention, there is provided a method of manufacturing a semiconductor device, the method comprising: loading a substrate into a process chamber; forming a film on the substrate by supplying a first process gas, which comprises at least one of a plurality of elements constituting the film and is capable of depositing a film by itself, to an inside of the process chamber through a first gas introducing part, and supplying a second process gas, which comprises at least one of the others of the plurality of elements constituting the film and is incapable of depositing a film by itself, to the inside of the process chamber through a second gas introducing part; unloading the substrate from the process chamber after the film is formed on the substrate; performing a first cleaning process so as to remove a first deposition substance attached to an inner wall of the first gas introducing part by supplying a cleaning gas to the first gas introducing part; and performing a second cleaning process so as to remove a second deposition substance attached to the inside of the process chamber and having a chemical composition different from that of the first deposition substance by supplying a cleaning gas to the inside of the process chamber through a third gas introducing part connected to a lower side of the process chamber at a position where the substrate is not placed, wherein when at least parts of the first cleaning process and the second cleaning process are simultaneously performed, a flowrate of the cleaning gas

supplied to the first gas introducing part is lower than a flowrate of the cleaning gas supplied through the third gas introducing part.

(Supplementary Note 11)

According to another embodiment of the present invention, there is provided a substrate processing apparatus comprising: a process chamber configured to accommodate a substrate; a first gas introducing part configured to supply a first process gas, which comprises at least one of a plurality of elements constituting a film to be formed on the substrate and is capable of depositing a film by itself, and a cleaning gas to an inside of the process chamber; a second gas introducing part configured to supply a second process gas, which comprises at least one of the others of the plurality of elements and is incapable of depositing a film by itself, to the inside of the process chamber; a third gas introducing part connected to a lower side of the process chamber at a position where the substrate is not placed and configured to supply a cleaning gas to the inside of the process chamber; an exhaust part configured to exhaust an inside atmosphere of the process chamber; and a control unit configured to control the first gas introducing part, the second gas introducing part, the third gas introducing part, and the exhaust part, wherein after a film is formed on the substrate by supplying the first and second process gases to the inside of the process chamber, the control unit controls the first gas introducing part, the second gas introducing part, the third gas introducing part, and the exhaust part, so as to remove a first deposition substance attached to an inner wall of the first gas introducing part by setting cleaning conditions according to accumulated supply time of the first process gas supplied to the inside of the process chamber through the first gas introducing part and supplying a cleaning gas to the first gas introducing part, and so as to remove a second deposition substance attached to the inside of the process chamber and having a chemical composition different from that of the first deposition substance by setting cleaning conditions according to an accumulated thickness of the film formed on the substrate and supplying a cleaning gas to the inside of the process chamber through the third gas introducing part.

(Supplementary Note 12)

Preferably, the cleaning conditions may be a pressure of the inside of the process chamber and a flowrate of the cleaning gas.

(Supplementary Note 13)

Preferably, the control unit may control the first gas introducing part, the third gas introducing part, and the exhaust part, such that a pressure of the inside of the process chamber when the cleaning gas is supplied through the third gas introducing part is lower than a pressure of the inside of the process chamber when the cleaning gas is supplied through the first gas introducing part.

(Supplementary Note 14)

Preferably, the first deposition substance may comprise at least one of the plurality of elements as a main component, and the second deposition substance may comprise the plurality of elements as main components.

(Supplementary Note 15)

According to another embodiment of the present invention, there is provided a substrate processing apparatus comprising: a process chamber configured to accommodate a substrate; a first gas introducing part configured to supply a first process gas, which comprises at least one of a plurality of elements constituting a film to be formed on the substrate and is capable of depositing a film by itself, and a cleaning gas to an inside of the process chamber; a second gas introducing part configured to supply a second process gas, which com-

prises at least one of the others of the plurality of elements and is incapable of depositing a film by itself, to the inside of the process chamber; a third gas introducing part connected to a lower side of the process chamber at a position where the substrate is not placed and configured to supply a cleaning gas to the inside of the process chamber; an exhaust part configured to exhaust an inside atmosphere of the process chamber; and a control unit configured to control the first gas introducing part, the second gas introducing part, the third gas introducing part, and the exhaust part, wherein after a film is formed on the substrate by supplying the first and second process gases to the inside of the process chamber, the control unit controls the first gas introducing part, the second gas introducing part, the third gas introducing part, and the exhaust part, so as to set pressure of the inside of the process chamber to a first pressure and supply a cleaning gas intermittently to the inside of the process chamber through the third gas introducing part, and so as to set the pressure of the inside of the process chamber to a second pressure lower than the first pressure and supply the cleaning gas continuously to the inside of the process chamber through the third gas introducing part.

(Supplementary Note 16)

According to another embodiment of the present invention, there is provided a cleaning control apparatus for a process chamber or a silicon-containing gas supply system of a silicon nitride film forming apparatus which is used to form a silicon nitride film having a predetermined silicon/nitrogen composition ratio on a substrate by alternately supplying a silicon-containing gas having a predetermined molecular weight and a nitriding source gas having a predetermined molecular weight, the cleaning control apparatus comprising: a cleaning request signal output unit comprising a memory unit configured to store an accumulated supply amount of silicon-containing gas molecules supplied to an inside of the process chamber through the silicon-containing gas supply system, the cleaning request signal output unit being configured to output a cleaning request signal so as to request cleaning of the silicon-containing gas supply system if the accumulated supply amount of the silicon-containing gas molecules stored in the memory unit becomes equal to or greater than a preset accumulated supply amount of silicon-containing gas molecules; and a cleaning request signal output unit comprising a memory unit configured to store an accumulated supply amount of nitriding source gas molecules supplied to the inside of the process chamber through a nitriding source gas supply system, the cleaning request signal output unit being configured to output a cleaning request signal so as to request cleaning of the nitriding source gas supply system if the accumulated supply amount of the nitriding source gas molecules stored in the memory unit becomes equal to or greater than a preset accumulated supply amount of nitriding source gas molecules.

(Supplementary Note 17)

According to another embodiment of the present invention, there is provided a cleaning control apparatus for a process chamber or a gas introducing part of a substrate processing apparatus which is used to form a predetermined film on a substrate placed in the process chamber by supplying a first process gas comprising at least one of a plurality of elements constituting the film and a second process gas comprising at least one of the others of the plurality of elements constituting the film to an inside of the process chamber through different gas introducing parts, respectively, the cleaning control apparatus comprising: a first monitoring unit configured to monitor a supply amount of the first process gas supplied to the inside of the process chamber through a first introducing part;

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a first adding unit configured to accumulate the monitored supply amount of the first process gas; a first memory unit configured to store the accumulated supply amount of the first process gas; a first comparison unit configured to compare the accumulated supply amount of the first process gas with a predetermined threshold value; a first signal output unit configured to output a cleaning request signal so as to request cleaning of an inner wall of the first introducing part if the accumulated supply amount of the first process gas is greater than the predetermined threshold value; a second monitoring unit configured to monitor a supply amount of the second process gas supplied to the inside of the process chamber through a second introducing part; a second adding unit configured to accumulate the monitored supply amount of the second process gas; a second memory unit configured to store the accumulated supply amount of the second process gas; a second comparison unit configured to compare the accumulated supply amount of the second process gas with a predetermined threshold value; and a second signal output unit configured to output a cleaning request signal so as to request cleaning of an inner wall of the second introducing part if the accumulated supply amount of the second process gas is greater than the predetermined threshold value.

What is claimed is:

1. A method of manufacturing a semiconductor device, comprising:

loading a substrate into a process chamber;

forming a film comprising a plurality of elements on the substrate by supplying a first source gas and a second source gas into the process chamber through a first gas introducing part and a second gas introducing part, respectively, the first source gas comprising at least one of the plurality of elements and the second source gas comprising at least one of the plurality of elements other than those of the first source gas;

unloading the substrate from the process chamber after the film is formed on the substrate;

performing a first cleaning process so as to remove a first deposition substance attached to an inner wall of the first gas introducing part by supplying a cleaning gas to the first gas introducing part, the first deposition substance comprising the at least one of the plurality of elements of the first source gas as a main component, wherein a cleaning condition is set according to an accumulated supply time of the first source gas supplied into the process chamber through the first gas introducing part; and

performing a second cleaning process so as to remove a second deposition substance attached to an inside of the process chamber and having a different chemical composition from that of the first deposition substance by supplying the cleaning gas into the process chamber through a third gas introducing part connected to a lower side of the process chamber at a position where the substrate is not placed, the second deposition substance comprising the plurality of elements as main components, wherein the cleaning condition is set according to an accumulated thickness of the film formed on the substrate,

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wherein the first source gas comprises a silicon-containing gas, and the second source gas comprises a nitrogen-containing gas, and

wherein the cleaning gas comprises:

at least one of nitrogen trifluoride (NF_3) gas, chlorine trifluoride (ClF_3) gas, fluorine (F_2) gas, hydrogen fluoride (HF) gas, chlorine (Cl_2) gas and boron trichloride (BCl_3) gas.

2. The method of claim 1, wherein the cleaning condition comprises a pressure of the inside of the process chamber and a flowrate of the cleaning gas.

3. The method of claim 1, wherein a pressure of the inside of the process chamber in the first cleaning process is set to be lower than that of the second cleaning process.

4. The method of claim 1, wherein the cleaning gas is continuously supplied to the first gas introducing part in the first cleaning process, and the cleaning gas is intermittently supplied into the process chamber in the second cleaning process.

5. A method of manufacturing a semiconductor device, comprising:

loading a substrate into a process chamber;

forming a film comprising a plurality of elements on the substrate by supplying a first source gas and a second source gas into the process chamber through a first gas introducing part and a second gas introducing part, respectively, the first source gas comprising at least one of the plurality of elements and the second source gas comprising at least one of the plurality of elements other than those of the first source gas;

unloading the substrate from the process chamber after the film is formed on the substrate;

performing a first cleaning process so as to remove a first deposition substance attached to an inner wall of the first gas introducing part by supplying a cleaning gas to the first gas introducing part, the first deposition substance comprising the at least one of a plurality of elements of the first source gas as a main component; and

performing a second cleaning process so as to remove a second deposition substance attached to an inside of the process chamber and having a different chemical composition from that of the first deposition substance by supplying the cleaning gas into the process chamber through a third gas introducing part connected to a lower side of the process chamber at a position where the substrate is not placed,

wherein a concentration of the cleaning gas supplied to the first gas introducing part is lower than that of the cleaning gas supplied to the third gas introducing part when at least portions of the first cleaning process and the second cleaning process are performed simultaneously,

wherein the first source gas comprises a silicon-containing gas, and the second source gas comprises a nitrogen-containing gas, and

wherein the cleaning gas comprises:

at least one of nitrogen trifluoride (NF_3) gas, chlorine trifluoride (ClF_3) gas, fluorine (F_2) gas, hydrogen fluoride (HF) gas, chlorine (Cl_2) gas and boron trichloride (BCl_3) gas.

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